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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Chang-Rong WU et al. Confirmation No: 9777
Appl. No. : 10/810,804
Filed : March 29, 2004
Title : Method And Composite Hard Mask For Forming Deep
Trenches In A Semiconductor Substrate

TC/A.U. : 2823
Examiner : F.L. Toledo

Docket No.: : WUCH3037/REF
Customer No: : 23364

AMENDMENT

Mail Stop Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

This is in response to the Official Action of September 13, 2005, in connection with the above-identified application. This response is timely filed.

Please amend the application as follows:

Amendments to the specification begin on page 2 of this paper.

Amendments to the claims are reflected in the listing of claims which begins on page 3 of this paper.

Remarks begin on page 5 of this paper.